2018년 2월 7일(수), 09:00-10:30 Room G (봉래॥+॥, 6층)

G. Device & Process Modeling, Simulation and Reliability 분과 [WG1-G] Advanced Devices II - Simulation and Reliability

WG1-G-1 09:00-09:15	RF 소자의 고 신뢰성 확보를 위한 RF인가 가속수명 시스템 설계 Yunho Kang, Sungsoo Chung, Sanga Kim, and Namho Kim QRT Incorporated
WG1-G-2 09:15-09:30	New Frequency-Dependent Modeling for Intrinsic Output Admittance of HR PD-SOI MOSFETs Changjo Lee and Seonghearn Lee Department of Electronics Engineering, Hankuk University
WG1-G-3 09:30-09:45	Mobility Calculation for GaN based Heterostructure: Effects of Variational Wave Function and Screening Suhyeong Cha and Sung-Min Hong School of Electrical Engineering and Computer Science, GIST
WG1-G-4 09:45-10:00	Characterization of Recombination Lifetime through Above-Bandgap Optical Transfer Curve in InGaAs MOSFETs Junyeap Kim, Heesung Lee, Jaewon Kim, Seong Kwang Kim, Han Bin Yoo, Jaewon Park, Sung-Jin Choi, Dae Hwan Kim, and Dong Myong Kim School of Electrical Engineering, Kookmin University
WF3-F-6 14:30-14:45	Simulation Study on the Effect of Unconformal Work-Function Metal Deposition on the Electrical Characteristic of Stacked-GAA MOSFET Sihyun Kim ¹ , Suhyeon Kim ¹ , Sangwan Kim ² , Euyhwan Park ¹ , Junil Lee ¹ , Ryoongbin Lee ¹ , Soyeon Kim ¹ , Hyun-Min Kim ¹ , Kitae Lee ¹ , Jong-Ho Lee ¹ , and Byung-Gook ¹ 1 ISRC and Department of Electrical and Computer Engineering, Seoul National University, ² Department of Electrical and Computer Engineering, Ajou University
WF3-F-6 14:30-14:45	Simulation Study on the Effect of Unconformal Work-Function Metal Deposition on the Electrical Characteristic of Stacked-GAA MOSFET Sihyun Kim ¹ , Suhyeon Kim ¹ , Sangwan Kim ² , Euyhwan Park ¹ , Junil Lee ¹ , Ryoongbin Lee ¹ , Soyeon Kim ¹ , Hyun-Min Kim ¹ , Kitae Lee ¹ , Jong-Ho Lee ¹ , and Byung-Gook ¹ 1SRC and Department of Electrical and Computer Engineering, Seoul National University, Department of Electrical and Computer Engineering, Ajou University